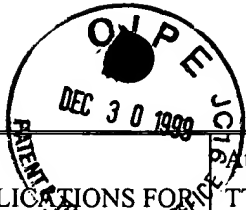


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| FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT | | | Attorney Docket No.: AM1084D01/T9320 TTC No.: 016301-009320US Applicant: David Cheung et al. | | Application No.: 09/418,818 | |
| | | | Filing Date: October 15, 1999 | | Group: Unknown | |
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| EXAMINER | DATE CONSIDERED |

Paul J. J... *5/7/01*

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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